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# Thyristor High Voltage, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	10 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
V <sub>TM</sub>	1.4 V			
I <sub>GT</sub>	60 mA			
T <sub>J</sub>	-40 °C to 125 °C			
Package	TO-220AB 3L			
Circuit configuration	Single SCR			

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

#### **DESCRIPTION**

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	10	A			
I <sub>RMS</sub>		16	A			
V <sub>DRM</sub> /V <sub>RRM</sub>	Range (1)	800, 1200	V			
I <sub>TSM</sub>		200	А			
V <sub>T</sub>	10 A, T <sub>J</sub> = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
T <sub>J</sub>	Range	-40 to +125	°C			

#### Note

(1) For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-16TTS08-M3	800	800	10			
VS-16TTS12-M3	1200	1200	10			

# VS-16TTS08-M3, VS-16TTS12-M3

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL		TEGT COMPLETIONS		VALUES		
PARAMETER	STINIBUL		TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 98 °C, 1	80° conduction, half sine wave	1	0		
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α	
Maximum peak, one-cycle,	L	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	70		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	ulse, no voltage reapplied	20	00		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	144		A <sup>2</sup> s	
waximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A <sup>2</sup> S	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied		2000		A²√s	
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25 °C		1.4		V	
On-state slope resistance	r <sub>t</sub>	T 405.00		T <sub>.1</sub> = 125 °C		1.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	1j=125 C		1	.1	V	
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V - Botod V A	0	.5		
waximum reverse and unect leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0		
Holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A 16TTS08PbF, 16TTS12PbF, $T_J$ = 25 °C		-	150	mA	
Maximum latching current	IL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		20	00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ °C, } V_{DRM} = R_g \text{ - k} = \text{Open}$		$T_J = T_J \text{ max., linear to } 80 \text{ °C, } V_{DRM} = R_g - k = Open$		V/µs	
Maximum rate of rise of turned-on current	dI/dt			150		A/µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	90		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60	mA	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35		
	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	3.0		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	v	
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	ij = 125 G, v <sub>DRM</sub> = nated value	2.0	mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9		
Typical reverse recovery time	t <sub>rr</sub>	T. – 105 °C	4	μs	
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110		

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C
Maximum thermal resistance, junction to case		$R_{thJC}$	DC operation	1.3	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		$R_{thCS}$	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf · cm
wounting torque	maximum			12 (10)	(lbf $\cdot$ in)
Mayling daving			Coop at the TO 200AR SI	16TTS08	
Marking device			Case style TO-220AB 3L		ΓS12

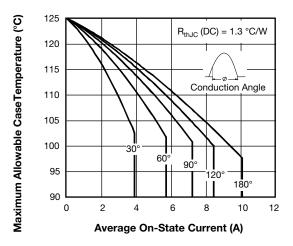


Fig. 1 - Current Rating Characteristics

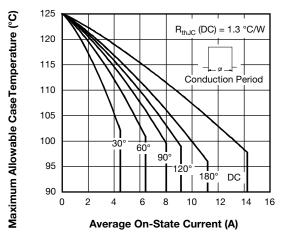


Fig. 2 - Current Rating Characteristics

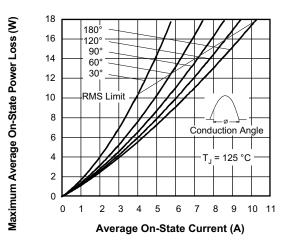


Fig. 3 - On-State Power Loss Characteristics

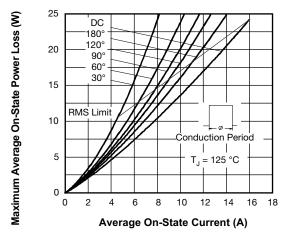


Fig. 4 - On-State Power Loss Characteristics



Peak Half Sine Wave On-State Current (A)

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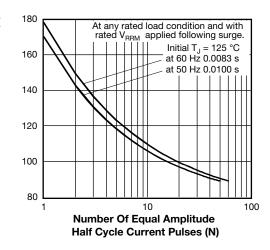


Fig. 5 - Maximum Non-Repetitive Surge Current

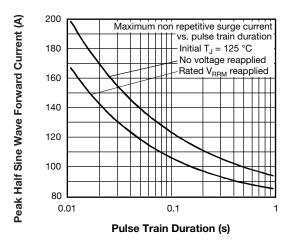


Fig. 6 - Maximum Non-Repetitive Surge Current

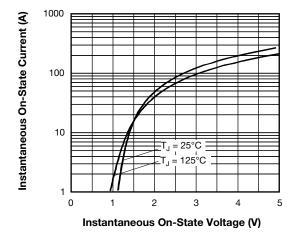


Fig. 7 - On-State Voltage Drop Characteristics

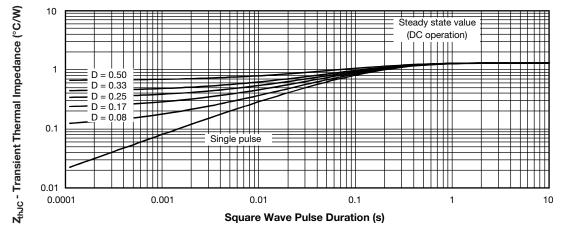


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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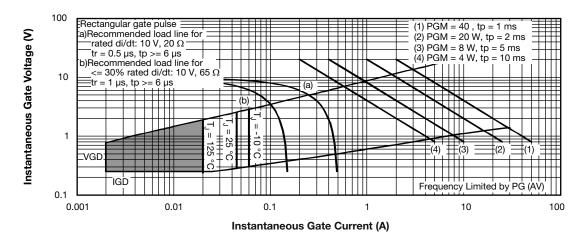


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

**Device code** 

1	2	3	4	5	6	7		
1 - 2 - 3 -	Cur Circ	ent ratir	guration	·	duct			
4 -	Pac	kage: TO-220 <i>i</i>	-					
5 -		e of silic	on: er grade		_			
6 - 7 -	Volt		e x 100			08 = 80 12 = 12		

ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08-M3	50	Antistatic plastic tubes			
VS-16TTS12-M3	50	Antistatic plastic tubes			

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

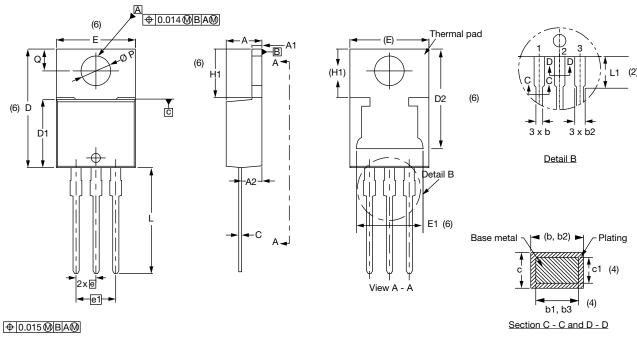
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96154		
Part marking information	www.vishay.com/doc?95028		



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### **TO-220AB 3L**

#### **DIMENSIONS** in millimeters and inches



Lead tip	
	1

Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183		D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055		E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115		E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040		е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4	e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068		H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4	L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024		L1	3.32	3.82	0.131	0.150	2
с1	0.36	0.56	0.014	0.022	4	ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3	Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							

### Notes

- $^{(1)}$  Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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